



Docket No.: 042390.P11362

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Brian S. Doyle

Application No.: 09/895,579

Filed: June 29, 2001

For: CREATION OF HIGH MOBILITY  
CHANNELS IN THIN-BODY SOI  
DEVICES 09895579

10/24/2002 GSTANLEY 00000001 022666 09895579

Examiner: David Nhu

Art Group: 2818

05:12:2001  
05:12:2002

84.00 CH  
234.00 CH

AMENDMENT AND RESPONSE TO THE OFFICE ACTION

Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, DC 20231-9998

Sir:

In response to the outstanding Office Action mailed May 1, 2002, please amend the above-identified Application as follows:

**IN THE SPECIFICATION**

Please replace the heading on page 1, line 6, with the following rewritten heading:

-- DESCRIPTION OF THE RELATED ART --

Please replace the sentence beginning on page 3, line 17, with the following rewritten sentence:

-- The relaxed SiGe layer has the thickness in the range of approximately from 0.1μm to 3.0μm.--

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App. No. 09 895,579

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